

INFORMATION DISCLOSURE CITATION IN AN APPLICATION				ATTY. DOCKET NO. 52775-025		SERIAL NO. <div style="font-size: 1.5em; text-align: center;">10/665,483</div>	
(PTO-1449)				APPLICANT Masahiro NAKAYAMA, et al.			
				FILING DATE September 22, 2003		GROUP <div style="font-size: 1.5em; text-align: center;">3723</div>	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code ¹ -Number ¹ -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
J.A. <div style="font-size: 2em; transform: rotate(-90deg); position: absolute; left: 50px; top: 50px;">↓</div>	—	WO99/23893	05/14/1999	SUMITOMO ELECTRIC IND LTD	—	(Japan w/English Abstract)	
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
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EXAMINER <div style="font-size: 1.5em; text-align: center;">Jacob Adam Jr.</div>				DATE CONSIDERED <div style="font-size: 1.5em; text-align: center;">11/30/04</div>			

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